

REMARKS

At the outset, the Examiner is thanked for the review and consideration of the present application.

The Examiner's Office Action dated July 30, 2002 has been received and its contents reviewed. Claims 2, 3, 6-8, 11, 12, 15-17, 19-35, and 37-67 are pending in the present application, of which claims 2, 3, 6-8, 19-24, 54, 57, 60 and 61 are independent.

Referring now to the detailed Office Action, claims 43-53, 55, 58, 61, 63, 65, and 67 are rejected under 35 U.S.C. §112, first paragraph, as containing subject matter which was not described in the specification in such a way as to reasonably convey to one skilled in the relevant art that the inventors at the time the invention was filed, had possession of the claimed invention. Specifically, the Examiner alleges that the specification never discloses a layer comprising silicon nitride on the channel formation region as claimed in claims 43-53, 55, and 58. Further, the Examiner alleges that the specification never discloses a pixel electrode over the transistor as claimed in claim 61. Applicants respectfully traverse the §112, first paragraph, rejection at least for the reasons provided below.

Applicants respectfully submit that the aforementioned features recited in claims 43-53, 55, and 58 are supported at least in, e.g., Fig. 1A and page 16, second paragraph of the specification. In Fig. 1A, a silicon nitride layer film 104 is formed on a semiconductor film 103 (a region becoming a channel formation region later is included), and the semiconductor film 103 is crystallized by laser irradiation through the silicon nitride film 104.

With respect to claim 61, Applicants respectfully assert that the feature of "a pixel electrode over a transistor" is supported at Figs. 10D and 10E. Nevertheless, Applicants have amended claim 61, as shown, above.

In view of the arguments and amendment set forth above, Applicants respectfully request reconsideration and withdrawal of the §112, first paragraph, rejection of claims <sup>43</sup>43-53, 55, 58, 61, 63, 65, and 67.

Claims 60-67 are rejected under 35 U.S.C. §103(a) as being unpatentable over Troxell et al. (U.S. Patent No. 4,851,363 – hereafter Troxell) in view of Ikeda (JP 59-121876), further in view of Shimada et al. (U.S. Patent No. 5,182,620). In response, Applicants respectfully traverse the rejection for the reason that, even if Troxell and Ikeda were combined, a laminated layer of aluminum nitride and silicon nitride is disclosed, but an insulating film comprising aluminum nitride and oxygen is not disclosed by Troxell and Ikeda. Therefore, the combination of Troxell

et al., Ikeda, and Shimada et al. is not proper in the §103(a) rejection of claims 60-67. Accordingly, the §103(a) rejection of claims 60-67 is respectfully requested to be reconsidered and withdrawn. **Bt**

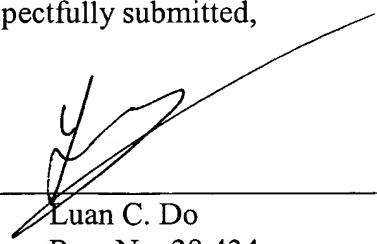
Claims 2, 3, 6, 7, 8, 11, 12, 15-17, 19, 20, 22-26, 28-35, 37, 38, 40-49, and 51-53 are rejected under the judicially created doctrine of obviousness-type double patenting as unpatentable over claims 15-26 of U.S. Patent No. 5,583,369 to Yamazaki et al. in view of Troxell et al. Further, claims 21, 27, 39, and 50 are rejected under the judicially created doctrine of obviousness-type double patenting as unpatentable over claims 15-26 of U.S. Patent No. 5,583,369 to Yamazaki et al. in view of Mano et al., and claims 54-67 are rejected under the judicially created doctrine of obviousness-type double patenting as unpatentable over claims 15-26 of U.S. Patent No. 5,583,369 to Yamazaki et al. in view of Shimada et al. In response to the double patenting rejection, Applicants are in the process of preparing a Terminal Disclaimer and will submit the same to the Examiner upon its completion.

Having responded to the rejection set forth in the outstanding non-Final Office Action, it is submitted that claims 2, 3, 6-8, 11, 12, 15-17, 19-35, and 37-67 are now in condition for allowance. An early and favorable Notice of Allowance is respectfully solicited. In the event that the Examiner is of the opinion that a brief telephone or personal interview will facilitate allowance of one or more of the above claims, the Examiner is courteously requested to contact Applicants' undersigned representative.

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Respectfully submitted,

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MARKED-UP VERSION OF AMENDED CLAIM:

61. A semiconductor device comprising:  
a substrate comprising a front surface and a rear surface;  
an insulating film comprising aluminum nitride and oxygen provided over said front surface of the substrate;  
a transistor provided over said insulating film, said transistor having at least a channel formation region, a gate insulating film adjacent to said channel formation region, and a gate electrode adjacent to said channel formation region with said gate insulating film interposed therebetween; [and]  
an insulating film over said transistor; and  
a pixel electrode over said [transistor] insulating film.

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